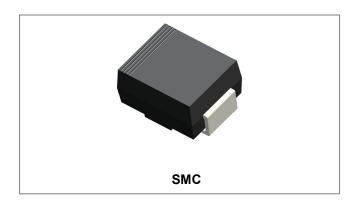






#### **SK320 SCHOTTKY RECTIFIER**



#### **Features**

- Small foot print, surface mountable
- Very low forward Voltage Drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Green Products in Compliance the ROHS Directive
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-		
Working Peak Reverse Voltage	$V_{RWM}$		200	V
DC Blocking Voltage	$V_{R}$			
Average Rectified Forward Current	1	50% duty cycle @T <sub>C</sub> =105°C, rectangular	2	Α
Average Reclined Forward Current	I <sub>F</sub> (AV)	wave form	J	^
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>c</sub> = 25 °C	110	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 3A, Pulse, T <sub>J</sub> = 25 °C	0.81	0.90	V
	V <sub>F2</sub>	@ 3A, Pulse, T <sub>J</sub> = 125 °C	0.70	0.80	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R_1} T_J = 25 ^{\circ}\text{C}$	0.0005	1.0	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_{R_1} T_J = 125  ^{\circ}\text{C}$	0.03	6.0	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	50	200	pF
Series Inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	$R_{ heta JL}$	DC operation	12	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	111	°C/W
Approximate Weight	wt	-	0.21	g

# **Ratings and Characteristics Curves**

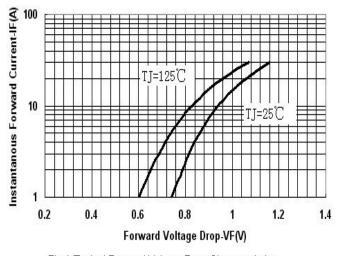


Fig.1-Typical Forward Voltage Drop Characteristics

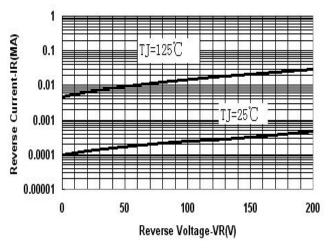


Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

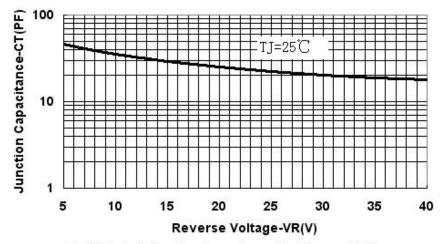


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage

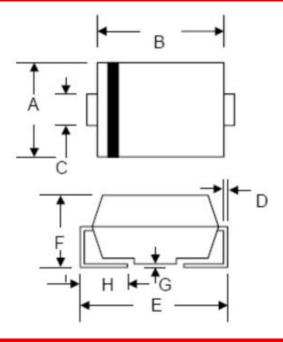
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#### **Mechanical Dimensions SMC**



CVMDOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	5.59	6.22	0.220	0.245	
В	6.60	7.11	0.260	0.280	
С	2.75	3.25	0.108	0.128	
D	0.152	0.305	0.006	0.012	
Е	7.75	8.25	0.305	0.325	
F	2.00	2.95	0.079	0.116	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.60	0.030	0.063	

# **Ordering Information**

Device Package		Shipping	
SK320	SMC (Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

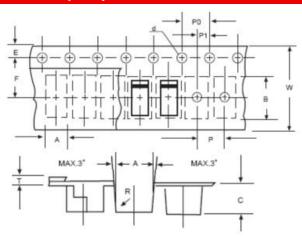
SK = Device Type
3 = Forward Current (3A)
20 = Reverse Voltage (200V)
YY = Year

WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

# **Carrier Tape Specification SMC**



SYMBOL	Millimeters		
STWIBUL	Min.	Max.	
Α	5.90	6.10	
В	8.20	8.40	
O	2.40	2.60	
d	1.40	1.60	
Е	1.40	1.60	
F	7.60	7.70	
Р	7.90	8.10	
P0	3.90	4.10	
P1	3.90	4.10	
Т	-	0.600	
W	15.80	16.20	

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